pH of the CMP polishing liquid is equal to or lower than 9.5.

5. The method for manufacturing a CMP polishing liquid according to claim 4, wherein the composite particle is obtained by mixing a liquid containing the first particle and the first component with a liquid containing the second component.

6. The method for manufacturing a CMP polishing liquid according to claim 4 or 5, wherein the precursor is a tetravalent cerium salt and the second component is a basic compound.

7. The method for manufacturing a CMP polishing liquid according to any one of claims 4 to 6, the method further comprising a step of dispersing the composite particle in water.

8. The method for manufacturing a CMP polishing liquid according to any one of claims 4 to 7, the method further comprising a step of washing the composite particle.

~~9. A method for manufacturing a composite particle, comprising a step of, in an aqueous solution that contains a first particle containing silica, a first component containing a precursor of cerium hydroxide, and a second component that is capable of reacting with the precursor to precipitate a second particle containing cerium hydroxide, precipitating the second particle by reacting the precursor and the second component to obtain a composite particle having a core including the first particle, and the second particle provided on the core.~~

~~10. The method for manufacturing a composite particle according to claim 9, wherein the composite particle is obtained by mixing a liquid containing the first particle and the first component with a liquid containing the second component.~~

~~11. The method for manufacturing a composite particle according to claim 9 or 10, wherein the precursor is a tetravalent cerium salt and the second component is a basic compound.~~